

# FDP6030BL/FDB6030BL

# N-Channel Logic Level PowerTrench® MOSFET

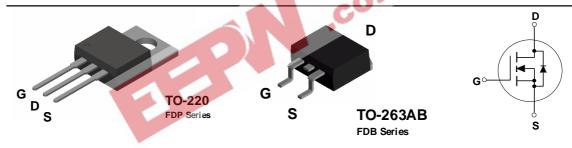
## **General Description**

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\text{DS(on)}}$  specifications resulting in DC/DC power supply designs with higher overall efficiency.

#### **Features**

- 40 A, 30 V.  $R_{DS(ON)} = 0.018~\Omega~@~V_{GS} = 10~V$   $R_{DS(ON)} = 0.024~\Omega~@~V_{GS} = 4.5~V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- 175°C maximum junction temperature rating.



Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDP6030BL	FDB6030BL	Units					
$V_{DSS}$	Drain-Source Voltage	3	30						
V <sub>GSS</sub>	Gate-Source Voltage	±	20	V					
I <sub>D</sub>	Maximum Drain Current - Continuous (Note 1)	4	10	Α					
	- Pulsed	1	20						
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> = 25°C	(	W						
	Derate above 25°C	0	W/°C						
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-65 to	°C						
Thermal Characteristics									
$R_{\theta_{JC}}$	Thermal Resistance, Junction-to-Case	2	.5	°C/W					
Reia	Thermal Resistance, Junction-to-Ambient	6:	2.5	°C/W					

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB6030BL	FDB6030BL	13"	24mm	800
FDP6030BL	FDP6030BL	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
DRAIN-S	OURCE AVALANCHE RAT	INGS (Note 1)					
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15 \text{ V}, I_{D} = 40 \text{ A}$			150	mJ	
I <sub>AR</sub>	Maximum Drain-Source Avalnche	Current			40	А	
Off Char	acteristics		•				
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V	
ΔBVpss ΔTι	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		23		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μд	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA	
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
On Char	acteristics (Note 1)		-0				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	. 1	1.6	3	V	
$\Delta V_{GS(th)}$ $\Delta T_1$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$	CX	-4.5		mV/°C	
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$		0.015 0.021 0.019	0.018 0.030 0.024	Ω	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$	40			Α	
<b>g</b> FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		30		S	
Dynamic	Characteristics Characteristics						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1160		pF	
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		250		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			100		pF	
	g Characteristics (Note 1)		!				
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		9	17	ns	
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		11	20	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			23	37	ns	
t <sub>f</sub>	Turn-Off Fall Time			8	16	ns	
Qg	Total Gate Charge	V <sub>DS</sub> = 15 V,		12	17	nC	
Q <sub>gs</sub>	Gate-Source Charge	$I_D = 20 \text{ A}, V_{GS} = 5 \text{ V}$		3.2		nC	
$Q_{gd}$	Gate-Drain Charge			3.7		nC	
	urce Diode Characteristics	and Maximum Patings	•				
<u> Diaiii-30</u> I <sub>s</sub>	Maximum Continuous Drain-Source				40	Α	
V <sub>SD</sub>	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$ (Note 1)		0.95	1.2	V	

Note: 1. Pulse Test: Pulse Width  $\leq 300~\mu s$ , Duty Cycle  $\leq 2.0\%$ 

## **Typical Characteristics**

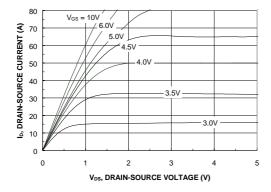


Figure 1. On-Region Characteristics.

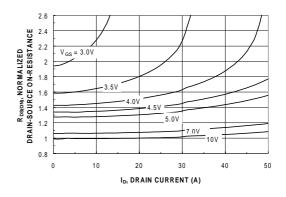


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

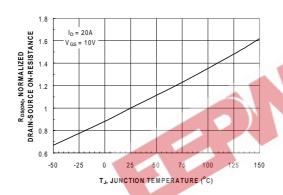


Figure 3. On-Resistance Variation with Temperature.

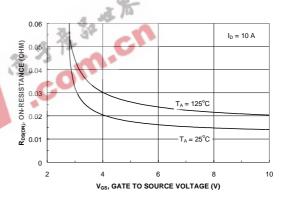


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

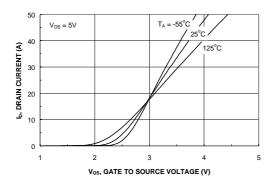


Figure 5. Transfer Characteristics.

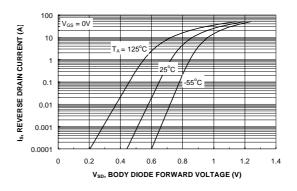
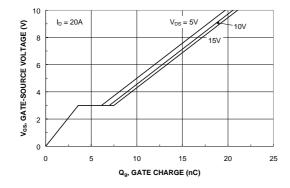


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics (continued)



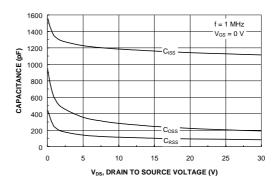
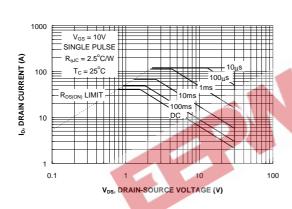


Figure 7. Gate-Charge Characteristics.

Figure 8. Capacitance Characteristics.



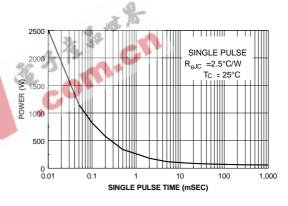


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

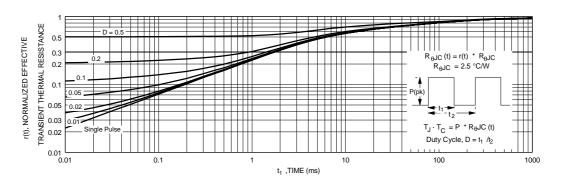
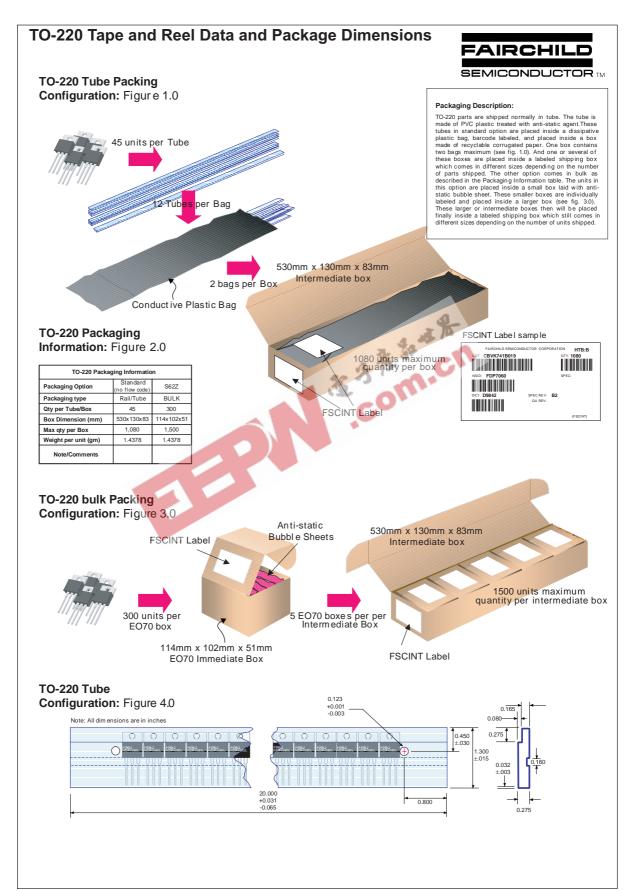
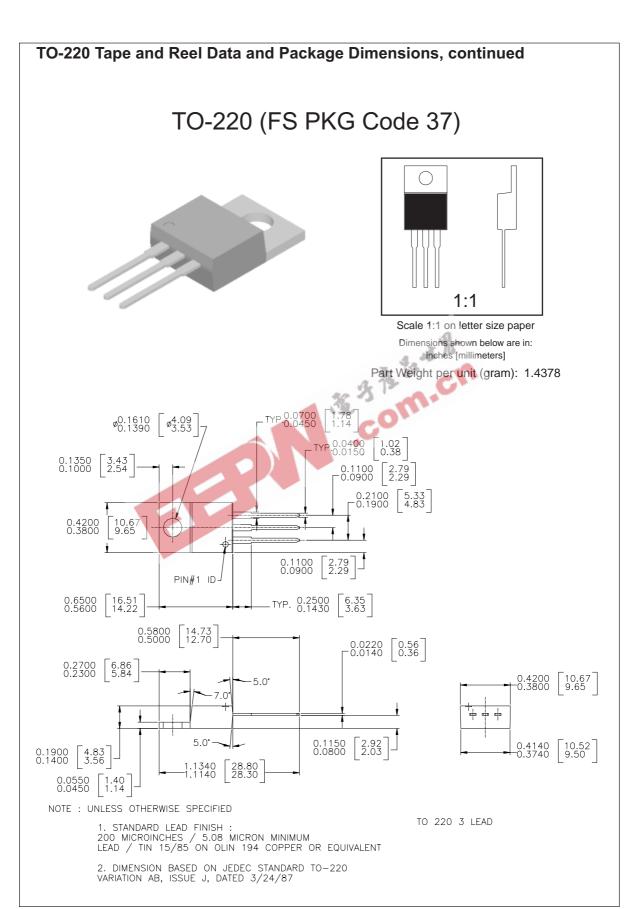
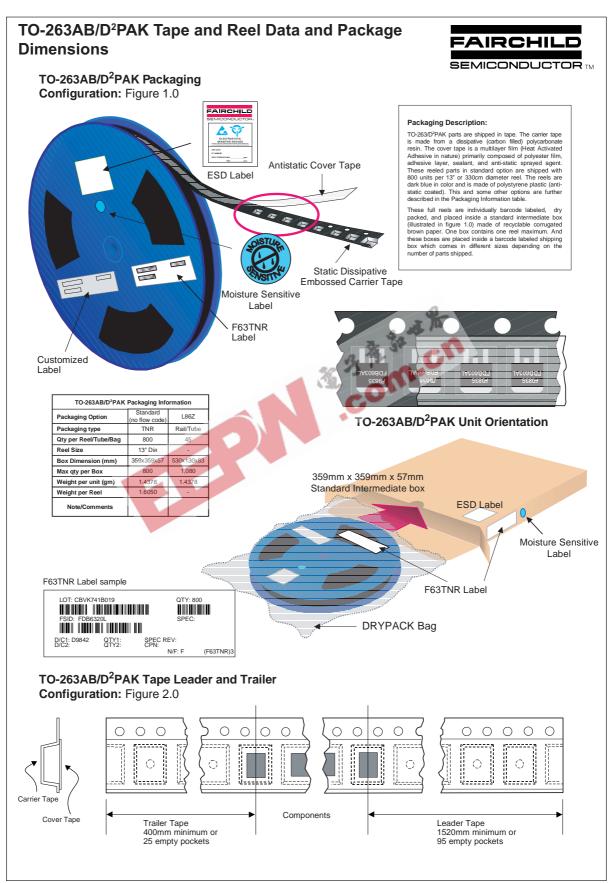


Figure 11. Transient Thermal Response Curve.

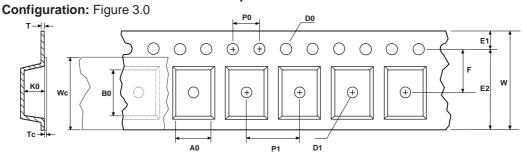






## TO-263AB/D<sup>2</sup>PAK Tape and Reel Data and Package Dimensions, continued

## TO-263AB/D<sup>2</sup>PAK Embossed Carrier Tape

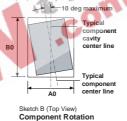




	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).





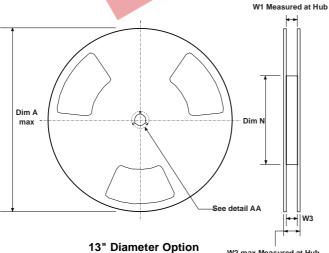


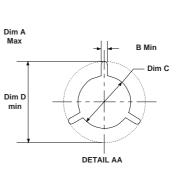
Sketch C (Top View)

Component lateral movement

## TO-263AB/D<sup>2</sup>PAK Reel Configuration:

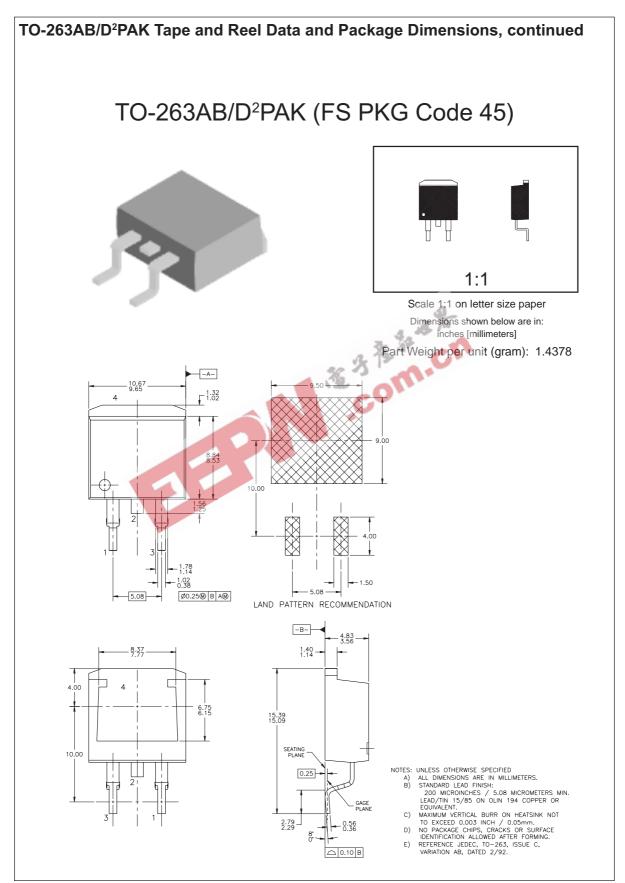
Figure 4.0





W2 max Measured at Hub

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4



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